#### (12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

## (19) World Intellectual Property Organization

International Bureau

(43) International Publication Date 02 November 2023 (02.11.2023)





(10) International Publication Number WO 2023/211361 A1

(51) International Patent Classification:

**G02B 6/42** (2006.01) **H01S 5/02** (2006.01) **H01S 5/00** (2006.01)

(21) International Application Number:

PCT/SG2022/050262

(22) International Filing Date:

28 April 2022 (28.04.2022)

(25) Filing Language:

English

(26) Publication Language:

English

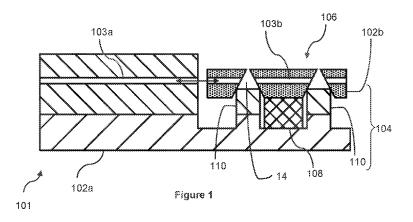
- (71) Applicant: COMPOUNDTEK PTE. LTD. [SG/SG]; 5 International Business, Park, #02-07a Mewah Building, Singapore 609914 (SG).
- (72) Inventor: LEE, Chee Wei; Block 141, Marsiling Road, #06-2074, Singapore 730141 (SG).
- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

#### **Published:**

— with international search report (Art. 21(3))

(54) Title: OPTICAL BENCH APPARATUS AND FABRICATION METHOD THEREFOR FOR HETEROGENEOUS LASER INTEGRATION



(57) **Abstract:** The present invention relates to an optical bench apparatus (100) for a heterogeneous laser integration. The optical bench apparatus (100) comprises a first chip (101) including a first substrate (102a), a first waveguide and an optical bench (104) formed on at least one portion of the first substrate (102a). At least one vertical alignment pillar (110) is formed on at least one portion of the optical bench (104). An active chip (106) is formed with a second waveguide. Furthermore, the present invention relates to a method for fabricating the optical bench apparatus.



OPTICAL BENCH APPARATUS AND FABRICATION METHOD

THEREFOR FOR HETEROGENEOUS LASER INTEGRATION

### FIELD OF THE INVENTION

The disclosures made herein relate generally to an optical apparatus, and more particularly to an optical bench apparatus and a method for fabricating an optical bench apparatus for a heterogeneous laser integration.

### **BACKGROUND OF THE INVENTION**

In general, silicon photonics enables the realization of various passive and active optical components, such as optical waveguides, splitters, filters, wavelength multiplexer (mux)/Demultiplexer (demux), modulators etc. However, due to the silicon's material property of having an indirect bandgap, it is poorly suited for making light sources such as laser or light emitting diodes. This requires compound semiconductor material systems such as Gallium Arsenide (GaAs) or Indium Phosphide (InP). As such, to realize a complete photonic integrated circuit (PIC), several techniques have been implemented to integrate light emitters onto a single chip with other active and passive functionalities. Flip chip bonding integration is one such technology, in which light emitter chips are flipped upside down and solder-bonded onto a common substrate called optical bench, and the light is coupled between them through precisely aligned waveguides. The technique is also an important packaging technology to allow passive alignment between optical chips that is both cost effective, more reliable and make

integration multiple chips on one optical bench possible. However, it has an inherit issue of semiconductor material systems (e.g., silicon material system) not being able to emit light.

United States Patent Publication No.: US 2016/0291265 A1 discloses optical alignment of two semiconductor chips to form a hybrid semiconductor device. One of the chips is flip-chip mounted in a recess formed in a main face of the other chip. Even though the said process allows quick and accurate alignment of the chips, the process of flipping needs complex and space consuming setup, which increases the cost and complexity of the manufacturing process.

Hence, there is a need for an optical bench apparatus and fabricating method therefor allowing quicker and more accurate alignment of the chips without a need for complex and space consuming setups.

## **SUMMARY OF THE INVENTION**

The present invention relates to an optical bench apparatus for heterogeneous laser integration. The optical bench apparatus comprises a first chip including a first substrate, a first waveguide and an optical bench on at least one portion of the first substrate and an active chip (106) formed with a second waveguide. At least one vertical alignment pillar is formed on at least one portion of the optical bench. At least one cavity is formed at a bottom portion of the active chip (106), wherein each cavity is configured to receive a top portion of a

corresponding vertical alignment pillar when the active chip is placed on the optical bench, such that the waveguides are aligned with one another to form an optical path between the first chip and the active chip.

In a preferred embodiment, the first substrate is a silicon-on-silicon substrate. The optical bench includes two Silicon dioxide ( $SiO_2$ ) layers and a silicon device layer sandwiched between the  $SiO_2$  layers.

More preferably, a thickness of the silicon device layer is in range of 220 nm to 340 nm and is top-cladded with 3 to 4  $\mu m$  of SiO<sub>2</sub>.

In one embodiment, the active chip comprises at least one of an edgeemitting laser and a photodetector.

Furthermore, the active chip and the optical bench are bonded using adhesives, wherein the adhesives include at least one of a solder paste and a metal solders.

Furthermore, the present invention relates to a method for fabricating an optical bench apparatus. The method comprises the steps of forming a first chip including a first substrate, a first waveguide and an optical bench, forming an active chip including a second waveguide and placing the active chip on the optical bench. The optical bench is on at least one portion of the first substrate

4

and at least one vertical alignment pillar is on at least one portion of the optical bench. The step of forming the active chip includes forming at least one cavity at a bottom portion of the active chip, wherein each cavity is configured to receive a top portion of a corresponding vertical alignment pillar when the active chip is placed on the optical bench, such that the waveguides are aligned with one another to form an optical path between the first chip and the active chip.

### BRIEF DESCRIPTION OF THE ACCOMPANYING DRAWINGS

The present invention will be fully understood from the detailed description given herein below and the accompanying drawings which are given by way of illustration only, and thus are not limitative of the present invention, wherein:

**FIGURE 1** shows a longitudinal sectional side view of an optical bench apparatus, according to one embodiment of the present invention.

**FIGURE 2** shows a longitudinal sectional top view of an optical bench apparatus, according to one embodiment of the present invention.

**FIGURE 3** is an example flow chart illustrating a method for fabricating the optical bench apparatus, according to one embodiment of the present invention.

#### DETAILED DESCRIPTION OF THE INVENTION

Detailed description of preferred embodiments of the present invention is disclosed herein. It should be understood, however, that the embodiments are

merely exemplary of the present invention, which may be embodied in various forms. Therefore, the details disclosed herein are not to be interpreted as limiting, but merely as the basis for the claims and for teaching one skilled in the art of the invention. The numerical data or ranges used in the specification are not to be construed as limiting. The following detailed description of the preferred embodiments will now be described in accordance with the attached drawings, either individually or in combination.

Accordingly, the embodiment herein is to provide an optical bench apparatus for a heterogeneous laser integration. The optical bench apparatus includes an optical bench formed on at least one portion of a first substrate and an active chip formed on at least one portion of a second substrate. At least one cavity is formed at a bottom portion of the active chip. At least one vertical alignment pillar is formed on at least one portion of the optical bench. When the active chip is placed on the optical bench, each cavity receives a corresponding pillar, such that a waveguide in the active chip is automatically aligned with a waveguide in the first chip, so as to provide an optical light path alignment between the two chips.

In the proposed optical bench apparatus, the optical bench apparatus including with one or multiple deeply etched pillars on the optical bench, together with an active chip with etched through cavities. Hence, the precision in optical light path alignment is achieved via the fabricated vertical alignment pillars on

the optical bench matched and aligned with the cavities on the active chip. In the proposed optical bench apparatus, the alignment between the active chip and optical bench is automatically achieved by the vertical pillars fabricated on the optical bench and the cavities fabricated on the active chip, through any conventional wafer process e.g. lithography and deep etching. Furthermore, since the cavities are formed at the bottom portion of the active chip, the active chip can be easily aligned with the optical bench without a need for flipping the active chip before mounting, which in turn avoids a need for a flipping chamber altogether while enabling easy visual alignment check, and thus minimizing cost, complexity and space requirements for the entire process.

The proposed optical bench apparatus creates a better heat dissipation channel from the bonded chip to the silicon optical bench substrate through the deep-etch recess and solder paste, which is typically an excellent heat conducting material. In the optical bench apparatus, the active chip does not need to be flipped (as required for common flip chip process), and hence, visual alignment check can be done.

Referring now to the drawings and more particularly to **FIGURE 1** through **FIGURE 2**, where similar reference characters denote corresponding features consistently throughout the figures, there are shown preferred embodiments.

and longitudinal sectional top view of an optical bench apparatus (100), according to one embodiment of the present invention. The optical bench apparatus (100) includes a first chip (101) formed with a first substrate (102a), a first waveguide (103a) and an optical bench (104) (also called as single hosting chip), an active chip (106) and adhesives. Preferably, the first substrate (102a) is a silicon-on-silicon substrate. The active chip (106) can include, for example, but not limited to an edge-emitting laser and a photodetector. The adhesives can include, for example, but not limited to a solder paste (108) and metal solders.

The optical bench (104) is formed on at least one portion of the first substrate (102a). The active chip (106) and the optical bench (104) are bonded using the adhesives. The optical bench (104) is formed by a silicon device layer sandwiched between two silicon dioxide (SiO<sub>2</sub>) layers. The bottom SiO<sub>2</sub>) layer is a 3 µm thick and the top SiO<sub>2</sub> layer is 3 to 4 µm thick. Furthermore, thickness of the silicon device layer is in range of 220 nm to 340 nm. The at least one vertical alignment pillar (110) is formed on at least one portion of the first substrate (102a) and the at least one cavity (112) is formed at a bottom portion of the active chip (106). A shape of the at least one vertical alignment pillar (110) can be a circular shape, rectangular shape, a square shape or the like. The active chip (106) includes a second substrate (102b), wherein each cavity (112) is formed at bottom of the second substrate (102b).

Each cavity (112) is configured to receive at least top portion of the corresponding vertical alignment pillar (110). One or more sidewalls of each cavity (112) configured such that the top portion of the vertical alignment pillar (110) abuts against the sidewalls of the cavity (112) as shown in FIGURE 1, to stop the vertical alignment pillar (110) from being further inserted inside the cavity (112).

The active chip (106) is bonded onto the optical bench (104), so as to provide a heat dissipation channel in the optical bench apparatus (100) as well as to form an electrical connection between the two chips (101, 106).

In an embodiment, after the standard optical device's fabrication process of both the active chip (106) and the first chip (101), the active chip (106), equipped with the cavities (11) designed precisely to match with the vertical pillars (110) on the optical bench (104), are aligned using a die attached machine (not shown) and the active chip (106) and the optical bench (104) are bonded together using adhesives that can include solder paste (108) or metal solders, as shown in **FIGURE 1**.

In an embodiment, the proposed optical bench apparatus (100) can be used to bond and integrate one or multiple chips, or a single chip with array of multiple devices (not shown), onto the optical bench (104).

FIGURE 2 is an example flow chart (S200) illustrating a method for fabricating the optical bench apparatus (100), according to one embodiment of the present invention. The method comprises the steps of: forming a first chip (201) including a first waveguide and an optical bench, forming an active chip (202) including a second waveguide and placing the active chip on the optical bench (203), such that the two waveguides are aligned to form an optical path between the two chips. While forming the active chip, at least one cavity is formed at a bottom portion of the active chip, wherein each cavity is configured to receive a top portion of a corresponding vertical alignment pillar on the optical bench, when the active chip is placed on the optical bench, such that the waveguides are aligned with one another to form the optical path.

The first chip includes a first substrate, wherein the optical bench is on at least one portion of the first substrate and at least one vertical alignment pillar is on at least one portion of the optical bench. Preferably, the first substrate is a silicon-on-silicon substrate.

The optical bench includes two Silicon dioxide (SiO<sub>2</sub>) layers and a silicon device layer sandwiched between the SiO<sub>2</sub> layers. Preferably, thickness of the silicon device layer is in a range of 220 nm to 340 nm. The silicon device layer is top-cladded with 3 to 4  $\mu$ m of SiO<sub>2</sub>. The active chip includes at least one of an edge-emitting laser and a photodetector.

The active chip is bonded to the optical bench using adhesives, wherein the adhesives include at least one of a solder paste and a metal solders e.g. gold tin solder.

In one embodiment, multiple deeply etched pillars are formed on the optical bench by any conventional fabrication process. Similarly, the cavities are etched at the bottom portion of the active chip through any conventional process. The pillars and the cavities are configured in such a way that each cavity receives at least a top portion of the corresponding pillar when the active chip is placed on the optical bench. One or more sidewalls of each cavity are configured to abut the top portion of the vertical alignment pillar when a predetermined length of the top portion of the pillar is inserted into the cavity.

By this way, the present invention ensures proper positioning of the active chip with respect to the optical bench, and thus realizing precise alignment between the waveguides without a need for flip mounting the active chip, which in turn avoids a need for a flipping chamber or assembly and thereby allowing quicker and more accurate alignment of the chips without a need for complex and space consuming setups.

The proposed method can be used to create a better heat dissipation channel from the bonded active chip to the first substrate (102a) through a deepetch recess and the solder paste (108), which is typically an excellent heat

conducting material. Since the cavities are formed at the bottom portion of the active chip, there is no need to flip the active chip while aligning it with the first chip, while enabling easy visual alignment check.

The proposed method provides a high precision requirement (<±0.5 um) than flip chip alignment between the active chip and the optical bench.

The terminology used herein is for the purpose of describing particular example embodiments only and is not intended to be limiting. As used herein, the singular forms "a", "an" and "the" may be intended to include the plural forms as well, unless the context clearly indicates otherwise. The terms "comprises", "comprising", "including" and "having" are inclusive and therefore specify the presence of stated features, integers, steps, operations, elements and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components and/or groups thereof. The method steps, processes and operations described herein are not to be construed as necessarily requiring their performance in the particular order discussed or illustrated, unless specifically identified as an order of performance. It is also to be understood that additional or alternative steps may be employed. The use of the expression "at least" or "at least one" suggests the use of one or more elements, as the use may be in one of the embodiments to achieve one or more of the desired objects or results.

(106).

PCT/SG2022/050262

## **CLAIMS**

## We claim:

- 1. An optical bench apparatus (100) for a heterogeneous laser integration, comprises:
  - i. a first chip (101) including a first substrate (102a), a first waveguide (103a) and an optical bench (104) formed on at least one portion of the first substrate (102a), wherein at least one vertical alignment pillar (110) is formed on at least one portion of the optical bench (104); and
  - an active chip (106) formed with a second waveguide (103b), ii. characterized in that: at least one cavity (112) is formed at a bottom portion of the active chip (106), wherein each cavity (112) is configured to receive a top portion of a corresponding vertical alignment pillar (110) when the active chip (106) is placed on the optical bench (104), such that the waveguides (103a, 103b) are aligned with one another to form an optical path between the first chip (101) and the active chip
- 2. The optical bench apparatus (100) as claimed in claim 1, wherein the first substrate (102a) is a silicon-on-silicon substrate.

3. The optical bench apparatus (100) as claimed in claim 1, wherein the optical bench (104) includes two Silicon dioxide (SiO<sub>2</sub>) layers and a silicon device layer sandwiched between the SiO<sub>2</sub> layers.

- 4. The optical bench apparatus (100) as claimed in claim 3, wherein a thickness of the silicon device layer is in the range of 220 nm to 340 nm.
- 5. The optical bench apparatus (100) as claimed in claim 3, wherein the silicon device layer is top-cladded with 3 to 4  $\mu$ m of SiO<sub>2</sub>.
- 6. The optical bench apparatus (100) as claimed in claim 1, wherein the active chip (106) comprises at least one of an edge-emitting laser and a photodetector.
- 7. The optical bench apparatus (100) as claimed in claim 1, wherein the active chip (106) and the optical bench (104) are bonded using adhesives, wherein the adhesives include at least one of a solder paste (108) and metal solders.
- 8. A method for fabricating an optical bench apparatus (100), comprises:
  - i. forming a first chip (101) including a first substrate (102a), a first waveguide (103a) and an optical bench (104), wherein the optical bench (104) is on at least one portion of the first substrate (102a)

PCT/SG2022/050262

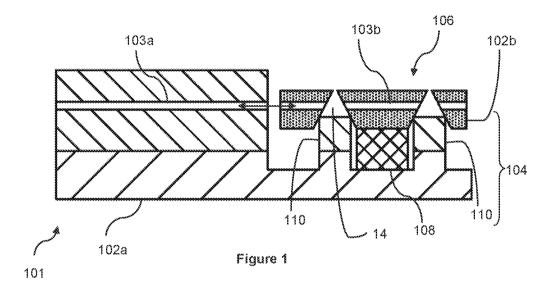
- and at least one vertical alignment pillar (110) is on at least one portion of the optical bench (104);
- ii. forming an active chip (106) including a second waveguide (103b); and
- iii. placing the active chip (106) on the optical bench (104),characterized in that the step of forming the active chip (106) includes:

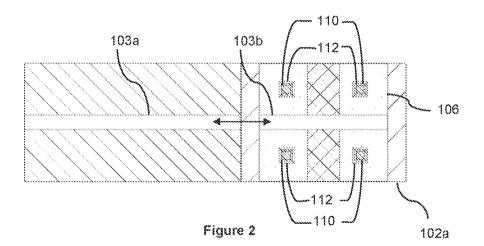
forming at least one cavity (112) at a bottom portion of the active chip (106), wherein each cavity (112) is configured to receive a top portion of a corresponding vertical alignment pillar (110) when the active chip (106) is placed on the optical bench (104), such that the waveguides (13a, 103b) are aligned with one another to form an optical path between the first chip (101) and the active chip (106).

- 9. The method as claimed in claim 8, wherein the first substrate (102a) is a silicon-on-silicon substrate.
- 10. The method as claimed in claim 8, wherein the optical bench (104) includes two Silicon dioxide (SiO<sub>2</sub>) layers and a silicon device layer sandwiched between the SiO<sub>2</sub> layers.

- 11. The method as claimed in claim 9, wherein a thickness of the silicon device layer is in range of 220 nm to 340 nm.
- 12. The method as claimed in claim 9, wherein the silicon device layer is top-cladded with 3 to 4  $\mu m$  of SiO<sub>2</sub>.
- 13. The method as claimed in claim 8, wherein the active chip (106) comprises at least one of an edge-emitting laser and a photodetector.
- 14. The method as claimed in claim 8, comprising the step of bonding the active chip (106) and the optical bench (104) using adhesives, wherein the adhesives include at least one of a solder paste (108) and a metal solders.

WO 2023/211361





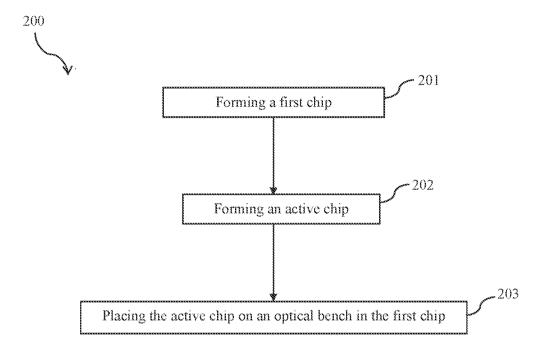


Figure 3

#### INTERNATIONAL SEARCH REPORT

International application No.

#### PCT/SG2022/050262

#### A. CLASSIFICATION OF SUBJECT MATTER

**G02B 6/42**(2006.01)i; **H01S 5/02**(2006.01)i; **H01S 5/00**(2006.01)i

According to International Patent Classification (IPC) or to both national classification and IPC

### B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

G02B 6/42(2006.01); G02B 6/136(2006.01); G02B 6/26(2006.01); H01J 5/02(2006.01); H01L 21/60(2006.01); H01L 27/146(2006.01); H01L 31/0236(2006.01); H01L 31/0352(2006.01)

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & Keywords: optical bench, chip alignment, pillar, cavity

#### C. DOCUMENTS CONSIDERED TO BE RELEVANT

Further documents are listed in the continuation of Box C.

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
DY	US 2016-0291265 A1 (CORIANT ADVANCED TECHNOLOGY, LLC) 06 October 2016 (2016-10-06) paragraphs [0068], [0072]-[0077], [0084], [0090], [0093], [0109]; claim 11; and figures 1-4, 10A-11B, 18A-18C	1-14
Y	US 9029759 B2 (HARPUNEET SINGH et al.) 12 May 2015 (2015-05-12) column 14, lines 47-62; and figures 19-20	1-14
A	US 2015-0063747 A1 (ACACIA COMMUNICATIONS INC.) 05 March 2015 (2015-03-05) paragraphs [0025]-[0037]; and figures 1-6	1-14
A	US 2017-0194522 A1 (SHIH-YUAN WANG et al.) 06 July 2017 (2017-07-06) paragraphs [0171]-[0347]; and figures 1-117	1-14
A	KR 10-2004-0090660 A (ELECTRONICS AND TELECOMMUNICATIONS RESEARCH INSTITUTE) 26 October 2004 (2004-10-26) paragraphs [0025]-[0052]; and figures 1a-4b	1-14

*	Special categories of cited documents:	"T"	later document published after the international filing date or priority
"A"	document defining the general state of the art which is not considered to be of particular relevance		date and not in conflict with the application but cited to understand the principle or theory underlying the invention
"D"	document cited by the applicant in the international application	"X"	document of particular relevance; the claimed invention cannot be
"E"	earlier application or patent but published on or after the international filing date		considered novel or cannot be considered to involve an inventive step when the document is taken alone
"L"	document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	"Y"	document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
"O"	document referring to an oral disclosure, use, exhibition or other means	"&"	document member of the same patent family
"P"	document published prior to the international filing date but later than the priority date claimed	œ	document memory of the same parent turnsy
Date	of the actual completion of the international search	Date	of mailing of the international search report
1	20.14 2022		21 M 2022
	30 May 2023		31 May 2023
Name	e and mailing address of the ISA/KR	Auth	orized officer
K 1		Auth	•
1: 3:	e and mailing address of the ISA/KR  Lorean Intellectual Property Office 89 Cheongsa-ro, Seo-gu, Daejeon		orized officer

See patent family annex.

International application No.

Patent document cited in search report			Publication date (day/month/year)	Pat	ent family member	r(s)	Publication date (day/month/year)
US	2016-0291265	A1	06 October 2016	EP	3213133	<b>A</b> 1	06 September 2017
				EP	3213133	<b>B</b> 1	25 December 2019
				US	10222565	B2	05 March 2019
				US	10598876	B2	24 March 2020
				US	10678005	B2	09 June 2020
				US	11256046	B2	22 February 2022
				US	2016-0116688	<b>A</b> 1	28 April 2016
				US	2016-0291269	<b>A</b> 1	06 October 2016
				US	2017-0045697	<b>A</b> 1	16 February 2017
				US	2018-0052290	<b>A</b> 1	22 February 2018
				US	2018-0259730	<b>A</b> 1	13 September 2018
				US	2019-0179091	<b>A</b> 1	13 June 2019
				US	2020-0183103	<b>A</b> 1	11 June 2020
				US	9500821	B2	22 November 2016
				US	9817197	B2	14 November 2017
				US	9989715	B2	05 June 2018
				WO	2016-069620	<b>A</b> 1	06 May 2016
				WO	2016-161150	<b>A</b> 1	06 October 2016
US	9029759	В2	12 May 2015	CN	104364908	A	18 February 2015
				CN	104364908	В	06 June 2017
				US	2013-0270419	<b>A</b> 1	17 October 2013
				WO	2013-155240	A2	17 October 2013
				WO	2013-155240	A3	05 December 2013
US	2015-0063747	A1	05 March 2015	US	9405073	B2	02 August 2016
US	2017-0194522	A1	06 July 2017	CN	105247189	A	13 January 2016
	2017 017 1322	211	00 <b>34</b> 1 <b>2</b> 01 7	CN	105264220	A	20 January 2016
				CN	105264220	В	23 March 2018
				CN	105556680	A	04 May 2016
				CN	105556680	В	22 December 2017
				CN	107078145	A	18 August 2017
				CN	107078145	В	07 May 2019
				CN	109155340	A	04 January 2019
				CN	110741301	A	31 January 2020
				CN	110741301	В	05 November 2021
				CN	110741302	A	31 January 2020
				CN	110741302	В	16 November 2021
				CN	110753846	A	04 February 2020
				CN	110753869	A	04 February 2020
				CN	110770553	A	07 February 2020
				CN	111133590	A	08 May 2020
				CN	112582387	A	30 March 2021
				EP	2999866	A1	30 March 2016
				EP	2999866	A4	26 April 2017
				EP	3000134	A2	30 March 2016
				EP	3000134	A4	04 January 2017
				EP	3000134	B1	10 March 2021
				EP	3008330	A1	20 April 2016
				EP	3008330	A4	16 August 2017
					2000220	4 1 1	10 / 10 8 10 1 20 1 /
				EP	3008330	<b>B</b> 1	05 February 2020

International application No.

Patent document cited in search report	Publication date (day/month/year)	P	atent family member	c(s)	Publication date (day/month/year)
	I * * /	EP	3411906	A1	12 December 2018
		EP	3411906	A4	09 October 2019
		EP	3638995	A1	22 April 2020
		EP	3638995	A4	31 March 2021
		EP	3639031	A1	22 April 2020
		EP	3639031	A4	05 May 2021
		EP	3639078	A1	22 April 2020
		EP	3639078	A4	31 March 2021
		EP	3639079	A1	22 April 2020
		EP	3639079	A4	24 February 2021
		EP	3639080	<b>A</b> 1	22 April 2020
		EP	3639080	A4	14 April 2021
		EP	3656000	A2	27 May 2020
		EP	3656000	A4	04 August 2021
		EP	3772104	A1	03 February 2021
		EP	3853504	A1	28 July 2021
		EP	3853504	A4	03 November 2021
		JP	2016-522346	A	28 July 2016
		JР	2016-526295	A	01 September 2016
		JP	2016-529431	A	23 September 2016
		JР	2018-508970	A	29 March 2018
		JP	2020-523613	A	06 August 2020
		JP	2020-523614	A	06 August 2020
		JР	2020-523615	A	06 August 2020
		JР	2020-523616		<del>-</del>
		JР	2020-523646	A	06 August 2020
		JP		A	06 August 2020 24 December 2020
		JP	2020-537816 2021-027358	A	22 February 2021
		JР		A B2	17 January 2018
			6260805 6602751		06 November 2019
		JP JP		B2	26 May 2021
			6875987 10-1874213	B2	
		KR		B1	03 July 2018
			10-2016-0009043 10-2016-0017086	A	25 January 2016
				A	15 February 2016
			10-2016-0039150 10-2020-0036849	A	08 April 2016
				A	07 April 2020
			10-2020-0040746 10-2020-0040747	A A	20 April 2020 20 April 2020
			10-2020-0040747	A	20 April 2020 20 April 2020
			10-2020-0040748	A	20 April 2020 22 April 2020
			10-2022-0019844	A	17 February 2022
		KR	10-2342988	B1	27 December 2021
		KR	10-2342988	в1 В1	27 December 2021 27 December 2021
		KR	10-2358584	В1	04 February 2022
		KR	10-2358384	В1	28 February 2022
		KR	10-2378095	в1 В1	28 February 2022 23 March 2022
		US	10-2378093	В2	23 March 2022 13 August 2019
		US	10446700	B2	15 October 2019
		US	10468543	B2	05 November 2019
		US		B2	04 February 2020
		03	10550961	D2	04 rebruary 2020

International application No.

Patent document cited in search report	Publication date (day/month/year)	Patent family member(s)			Publication date (day/month/year)
		US	10622498	B2	14 April 2020
		US	10670116	B2	02 June 2020
		US	10700225	B2	30 June 2020
		US	10807148	B2	20 October 2020
		US	10815968	B2	27 October 2020
		US	10895332	B2	19 January 2021
		US	10941749	B2	09 March 2021
		US	10947956	B2	16 March 2021
		US	10982645	B2	20 April 2021
		US	11111898	B2	07 September 2021
		US	11121271	B2	14 September 2021
		US	2012-0115662	A1	10 May 2012
		US	2012-0113002	A1	27 September 2012
		US	2012-0299301	A1	29 November 2012
		US	2012-0299301	A1	17 October 2013
		US	2013-0274030	A1	03 April 2014
		US	2014-0094338	A1	22 May 2014
		US	2014-0137676	A1	<del>-</del>
					22 May 2014
		US US	2014-0241855	A1	28 August 2014
			2014-0290616	A1	02 October 2014
		US	2015-0204421	A1	23 July 2015
		US	2015-0357951	A1	10 December 2015
		US	2016-0010620	A1	14 January 2016
		US	2016-0025001	A1	28 January 2016
		US	2016-0126381	A1	05 May 2016
		US	2016-0169353	A1	16 June 2016
		US	2016-0254407	<b>A</b> 1	01 September 2016
		US	2016-0307939	A1	20 October 2016
		US	2016-0308075	A1	20 October 2016
		US	2017-0030326	A1	02 February 2017
		US	2017-0236131	<b>A</b> 1	17 August 2017
		US	2018-0038340	A1	08 February 2018
		US	2018-0045334	A1	15 February 2018
		US	2018-0102442	<b>A</b> 1	12 April 2018
		US	2018-0195582	A1	12 July 2018
		US	2018-0361463	<b>A</b> 1	20 December 2018
		US	2019-0019899	A1	17 January 2019
		US	2019-0048845	A1	14 February 2019
		US	2019-0049041	A1	14 February 2019
		US	2019-0288132	<b>A</b> 1	19 September 2019
		US	2020-0028000	<b>A</b> 1	23 January 2020
		US	2020-0088156	<b>A</b> 1	19 March 2020
		US	2020-0095974	<b>A</b> 1	26 March 2020
		US	2020-0116277	<b>A</b> 1	16 April 2020
		US	2020-0191120	<b>A</b> 1	18 June 2020
		US	2020-0192072	A1	18 June 2020
		US	2021-0180559	<b>A</b> 1	17 June 2021
		US	2021-0242354	<b>A</b> 1	05 August 2021
		US	8388481	B2	05 March 2013
		US	8485933	B2	16 July 2013

International application No.

Patent document cited in search report	Publication date (day/month/year)	I Patent family member(c)		Publication date (day/month/year)	
	•			B2	04 February 2014
		US	8702552	B2	22 April 2014
		US	8986149	B2	24 March 2015
		US	8992370	B2	31 March 2015
		US	9017208	B2	28 April 2015
		US	9151269	B2	06 October 2015
		US	9169772	B2	27 October 2015
		US	9303733	B2	05 April 2016
		US	9371775	B2	21 June 2016
		US	9476401	B2	25 October 2016
		US	9490736	B2	08 November 2016
		US	9496435	B2	15 November 2016
		US	9506534	B2	29 November 2016
		US	9525084	B2	20 December 2016
		US	9530905	B2	27 December 2016
		US	9818893	B2	14 November 2017
		US	9912209	B2	06 March 2018
		WO	2011-011358	A2	27 January 2011
		WO	2011-011358	A3	28 April 2011
		WO	2014-189640	<b>A</b> 1	27 November 2014
		WO	2014-190189	A2	27 November 2014
		WO	2014-190189	A3	22 January 2015
		WO	2014-190189	A9	07 January 2016
		WO	2014-200622	<b>A</b> 1	18 December 2014
		WO	2015-160623	$\mathbf{A}1$	22 October 2015
		WO	2016-081476	<b>A</b> 1	26 May 2016
		WO	2017-112747	$\mathbf{A}1$	29 June 2017
		WO	2018-228508	$\mathbf{A}1$	20 December 2018
		WO	2018-228574	<b>A</b> 1	20 December 2018
		WO	2018-228575	$\mathbf{A}1$	20 December 2018
		wo	2018-228576	<b>A</b> 1	20 December 2018
		WO	2018-228577	A1	20 December 2018
		wo	2019-018846	A2	24 January 2019
		WO	2019-018846	A3	28 March 2019
		wo	2019-089437	<b>A</b> 1	09 May 2019
		WO	2020-139863	<b>A</b> 1	02 July 2020
KR 10-2004-0090660	A 26 October 2004	KR	10-0524672	B1	01 November 2005